



NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE8295AK uses advanced trench technology and design to provide excellent $R_{\rm DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

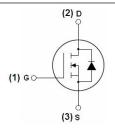
- $V_{DS} = 82V, I_D = 95A$ $R_{DS(ON)} < 7.0 \text{ m}\Omega$ @ $V_{GS} = 10V$ (Typ:6mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE8295AK	NCE8295AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	82	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous	I _D	95	А	
Drain Current-Continuous(T _C =100 ℃)	I _D (100°C)	67	А	
Pulsed Drain Current	I _{DM}	320	А	
Maximum Power Dissipation	P _D	170	W	
Derating factor		1.13	W/°C	
Single pulse avalanche energy (Note 5)	Eas	529	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	Rejc	0.88	°C/W



NCE8295AK

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Off Characteristics	-		'		1	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	82	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =82V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	6	7.0	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	-	50	-	S
Dynamic Characteristics (Note4)					1	
Input Capacitance	C _{lss}	V 05VV 0V	-	5633	-	PF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	268	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	226	-	PF
Switching Characteristics (Note 4)			'			
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	t _r	VDD=40V,RL=15Ω	-	12	-	nS
Turn-Off Delay Time	t _{d(off)}	RG=2.5Ω,VGS=10V	-	56	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg	\/ 40\/ 50A	-	109.3	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =50A,	-	35.1	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	25.8	-	nC
Drain-Source Diode Characteristics	-		'		1	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =95A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	95	Α
Reverse Recovery Time	t _{rr}	Tj=25°C,I _F =100A	-		37	nS
Reverse Recovery Charge	Qrr	di/dt=100A/µs ^(Note3)	-		58	nC

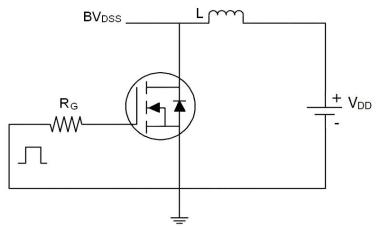
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25 Ω

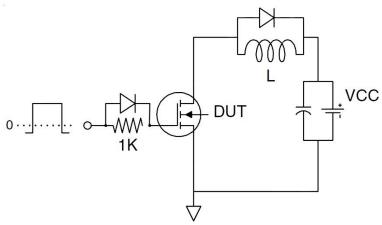


Test Circuit

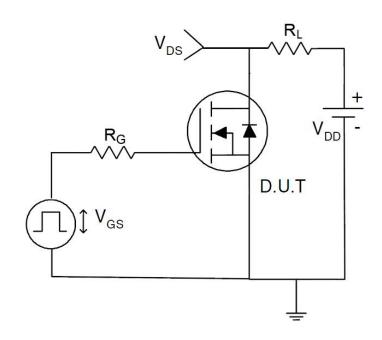
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Pb Free Product



Typical Electrical and Thermal Characteristics (Curves

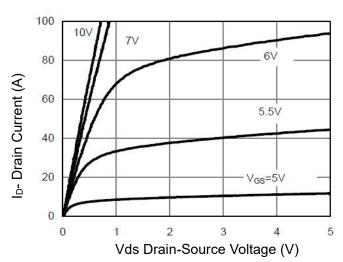


Figure 1 Output Characteristics

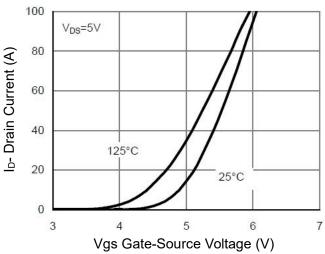


Figure 2 Transfer Characteristics

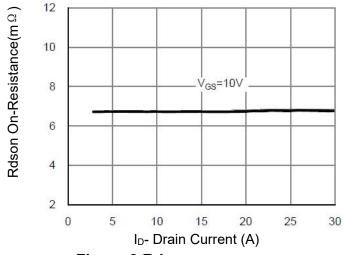


Figure 3 Rdson- Drain Current

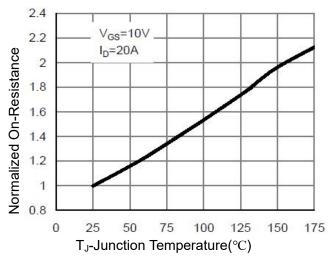


Figure 4 Rdson-Junction Temperature

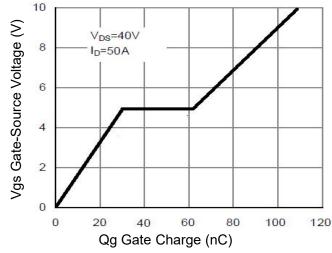


Figure 5 Gate Charge

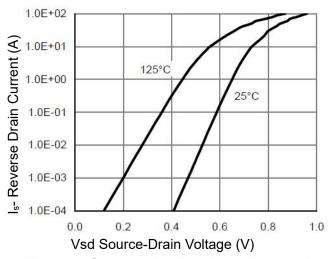
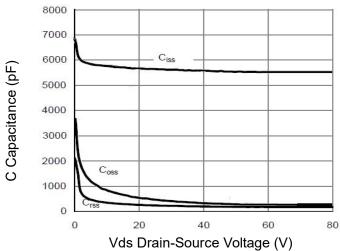


Figure 6 Source- Drain Diode Forward

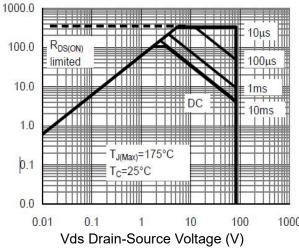




240 200 Power Dissipation (W) 160 120 80 40 0 0 25 75 100 125 150 175 T_J-Junction Temperature(°C)

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



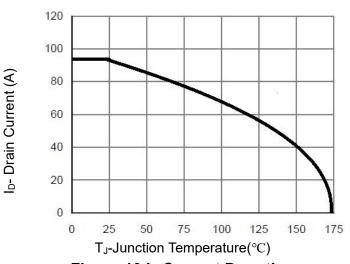


Figure 8 Safe Operation Area

Figure 10 I_D Current De-rating

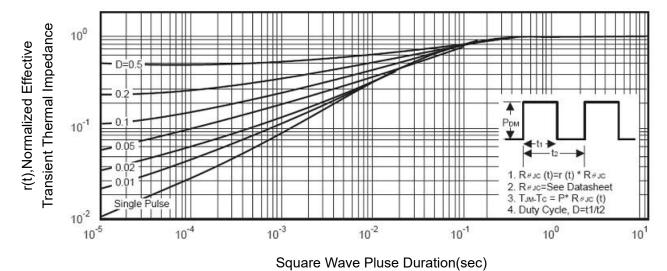
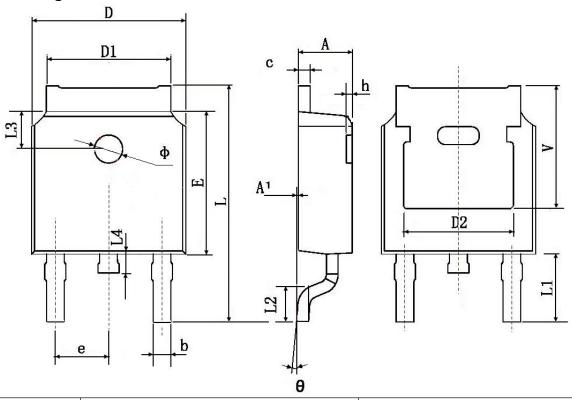


Figure 11 Normalized Maximum Transient Thermal Impedance

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TO-252 Package Information



Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83	0 TYP.	0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063	TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211	TYP.	



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NCE8295AK

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